RB551V-30

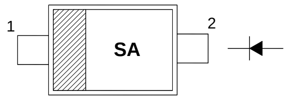
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type
- Ultra low V_F
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**SA**"
Simplified outline SOD-323 and symbol

Applications

- High frequency rectification switching regulation

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	30	V
DC Reverse Voltage	V_R	20	V
Mean Rectifying Current	I_O	0.5	A
Peak Forward Surge Current (60 Hz for 1 Cyc.)	I_{FSM}	2	A
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_s	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA at I_F = 500 mA	V_F	 0.36 0.47	V
Reverse Current at V_R = 20 V	I_R	100	µA

Note: ESD sensitive product handling required.

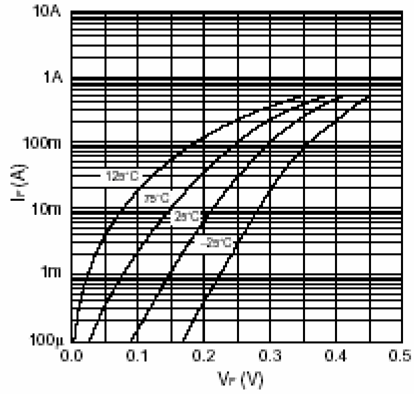


Fig.1 Forward characteristics

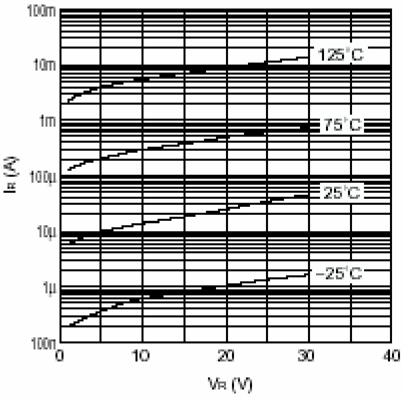


Fig.2 Reverse characteristics

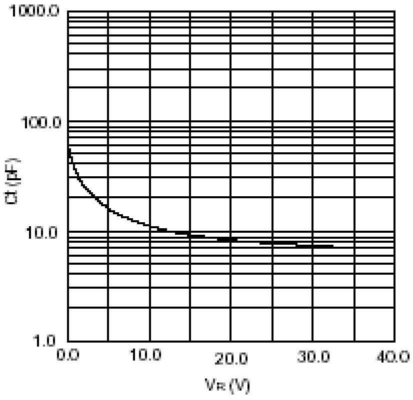


Fig.3 Capacitance between terminals characteristics

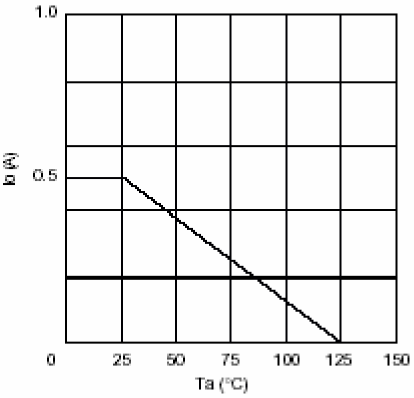
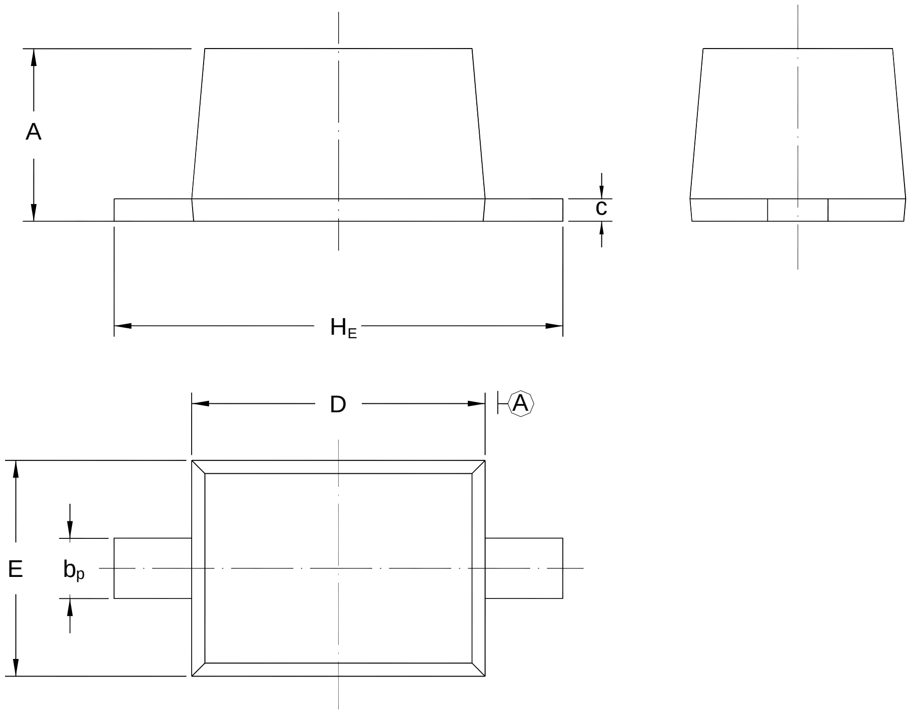


Fig.4 Derating curve

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-323**



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.00	1.80 1.60	1.35 1.15	2.80 2.30